

New Jersey Semi-Conductor Products, Inc.

**20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.**

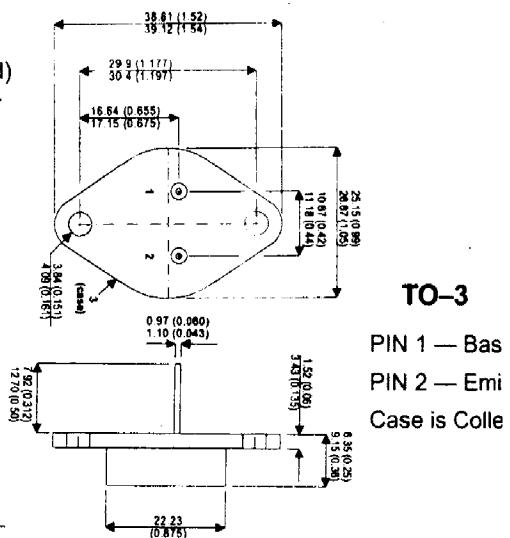
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NPN MULTI - EPITAXIAL POWER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^\circ\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage ($I_E = 0$)	300V
V_{CEX}	Collector – Emitter Voltage ($V_{BE} = -1.5V$)	300V
V_{CEO}	Collector – Emitter Voltage ($I_B = 0$)	250V
V_{EBO}	Emitter – Base Voltage ($I_C = 0$)	7V
I_C	Collector Current	20A
I_{CM}	Peak Collector Current ($t_p = 10 \text{ ms}$)	25A
I_B	Base Current	4A
P_{tot}	Total Power Dissipation at $T_{case} \leq 25^\circ\text{C}$	150W
T_{stg}	Storage Temperature	-65 to 200°C
T_J	Junction Temperature	200°C



ELECTRICAL CHARACTERISTICS ($T_{case} = 25^\circ\text{C}$ unless otherwise stated)

Electrical Characteristics (Case = 20°C Unless Otherwise Stated)						
Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$V_{CEO(sus)^*}$	Collector - Emitter Sustaining Voltage	$I_C = 0.2\text{mA}$	250			V
V_{EBO}	Emitter – Base Voltage	$I_E = 50\text{mA}$	7			V
I_{CEO}	Collector Cut-off Current	$V_{CE} = 200\text{V}$			1.5	mA
I_{CEX}	Collector Cut-off Current	$V_{CE} = 300\text{V}$	$V_{BE} = -1.5\text{V}$		1.5	mA
		$V_{CE} = 300\text{V}$	$V_{BE} = -1.5\text{V}$		6	
			$T_C = 125^\circ\text{C}$			
I_{EBO}	Emitter Cut-off Current	$I_C = 0$	$V_{EB} = 5\text{V}$		1	mA
$V_{CE(sat)^*}$	Collector – Emitter Saturation Voltage	$I_C = 5\text{A}$	$I_B = 0.5\text{A}$	0.22	1	V
	Saturation Voltage	$I_C = 10\text{A}$	$I_B = 1.25\text{A}$	0.5	1.5	
$V_{BE(sat)^*}$	Base – Emitter Saturation Voltage	$I_C = 10\text{A}$	$I_B = 1.25\text{A}$	1.23	1.5	V
h_{FE^*}	DC Current Gain	$I_C = 5\text{A}$	$V_{CE} = 4\text{V}$	20		60
		$I_C = 10\text{A}$	$V_{CE} = 4\text{V}$	10		
$I_{S/b}$	Second Breakdown	$V_{CE} = 30\text{V}$	$t = 1\text{s}$	5		
	Collector Current	$V_{CE} = 140\text{V}$	$t = 1\text{s}$	0.15		A
f_T	Transition Frequency	$I_C = 1\text{A}$	$V_{CE} = 15\text{V}$	8		MHz
		$f = 10\text{MHz}$				
t_{on}	Turn-On Time	$I_C = 10\text{A}$	$I_{B1} = 1.25\text{A}$		0.28	1
		$V_{CC} = 150\text{V}$				
t_s	Storage Time	$I_C = 10\text{A}$	$I_{B1} = 1.25\text{A}$		1.45	2
t_f	Fall Time	$I_{B2} = -1.25\text{A}$	$V_{CC} = 150\text{V}$	0.23	0.5	μs

THERMAL CHARACTERISTICS

R_{θJC} Thermal Resistance Junction to Case 1.17 °C/W

N S

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.